

#### **FEATURES**

- $45 \text{ m}\Omega$  High-Side MOSFET
- 1.0~4.0 A (typ.) Adjustable Current Limit
- Low Average Current in OUT shorted GND
- Support Apple® Devices fast charging (Apple®
- 2.1A / 2.4A mode)
- Support Samsung Galaxy Tab Devices fast Charging
- Support BC1.2 & YD/T 1591-2009 Charging Spec
- Built-in Soft-Start
- Support single layer PCB layout.
- $4.5 \sim 6.5 \text{V}$  Single Supply Operation.
- Available EMSOP8/ESOP8 package.

#### **APPLICATIONS**

- USB Charger
- USB Wall Adapter
- Car Charger

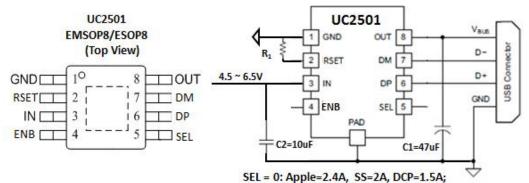
# PACKAGE AND APPLICATION

### DESCRIPTION

The UC2501 integrated USB charger emulators with automatic host charger identification circuitry and high performance adjustable current limiting power switch. An automatic USB charger identification circuit allows mobile power supply can automatically provides the correct modes on the data lines to charger compliant devices among the Apple, Samsung and BC1.2 modes.

The UC2501 is a  $45m\Omega$  power switch intended for applications where heavy capacitive loads and short-circuits are likely to be encountered. This also provides hiccup mode when OUT voltage is less than 2.85V or OTSD.

The UC2501 provides an ENB pin to turn on or turn off UC2501 and an SEL pin to select 10W or 12W mode in application.



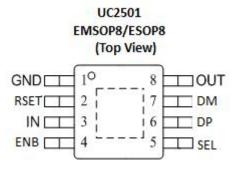
SEL = 1 or Floating: Apple=2.1A, SS=2A, DCP=1.5A; ENB is floating or pull down with 10k Resistor if not used

#### **ORDING INFORMATION**

Part Number	Package Type	Package Qty	Op Temp(°C)	Mark
UC2501	EMSOP8	3000	-40~85	UC2501
UC2501	ESOP8	3000	-40~85	UC2501



#### PINOUT

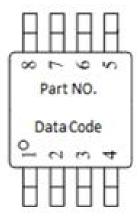


#### **PIN FUNCTIONS**

NAME	TYPE <sup>(1)</sup>	DESCRIPTION
GND	G	Ground connection
RSET	Ι	External resistor used to set current-limit threshold;
IN	P/I	Power supply/Input voltage connected to Power Switch; connect a 1 $\mu$ F or greater ceramic capacitor from IN to GND as close to the IC as possible
ENB	Ι	Enable input, logic low turns on UC2501
SEL	Ι	Logic-level control input; When it is high or floating, DP/DM operate in 2.1A mode, when it is Low, DP/DM operate in 2.4A mode;
DP	O/I	DP date line to connector, output for hand-shake voltage to portable equipment, high impedance while disabled
DM	O/I	DM data line to connector, input for hand-shake voltage from portable equipment high impedance while disabled
OUT	0	Power-switch output, connected to VBUS of USB; connect a $22\mu$ F or greater ceramic capacitor from OUT to GND as close to the IC as possible
	GND RSET IN ENB SEL DP DM	GND G RSET I IN P/I ENB I SEL I DP O/I DM O/I

(1) G = Ground, I = Input, O = Output, P = Power
(2)

### **MARK INFORMATION**





# ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

Over recommended operating free-air temperature range (unless otherwise noted)

PAI	MIN	MAX	UNIT		
Supply Voltage Range	IN	-0.3	7.0		
Input voltage range DP,DM		-0.3	5.8	V	
Continuous output sink current	DP input current, DM input current		35		
Continuous output source current	DP output current, DM output current		35	mA	
	IN		2	137	
ESD rating, Human Body Model (HBM)	DP, DM		2	kV	
Operating Junction Temperature	Тл	-40	150	ംറ	
Storage Temperature Range	T <sub>stg</sub>	-65	150	Ĵ	

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC			UNIT
0	EMSOP8 Package thermal impedance <sup>(1)</sup>	65	°C/W
θ <sub>JA</sub>	ESOP8 Package thermal impedance <sup>(1)</sup>	42	°C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

#### **RECOMMENDED OPERATING CONDITIONS**

	PARAMETER		MAX	UNIT
V <sub>IN</sub>	Input voltage of IN	4.5	6.5	V
V <sub>DP/DM</sub>	DP data line input voltage		5.5	v
I <sub>DP/DM</sub>	Continuous sink/source current		±10	mA
R <sub>SET</sub>	Resistance of R <sub>SET</sub>	13	100	kΩ
I <sub>OUT</sub>	Continuous sink/source current	1000	4000	mA
TJ	Operating Junction Temperature	-40	125	°C



#### **ELECTRICAL CHARACTERISTICS**

Conditions are:  $TA = 25^{\circ}C$ , VIN = SEL = 5.0 V, ENB = GND and  $RSET = 33.0k\Omega$ . Positive current are into pins. All voltages are with respect to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
		Power Switch				
R <sub>DSON</sub>	EMSOP8 Package	I <sub>OUT</sub> =1A		45		mΩ
KDSON	ESOP8 Package	IOUT-IA		55		11122
		Current Limit				
Ios	OUT current limited	BIN1:R <sub>SET</sub> =18.7k	2.50	2.70	2.90	А
108		BIN2:R <sub>SET</sub> =20.5K	2.50	2.70	2.90	
		Enable Pin (ENB)	1	1		1
$V_{\text{ENB}}$	ENB threshold voltage, falling		0.8	1.33	2.3	v
V <sub>ENB_H</sub> ys	Hysteresis			150		mV
R <sub>PD</sub>	Pull Down Resistor		200	290	380	kΩ
		Hiccup Mode				
V <sub>OUT_S</sub> Hort	OUT Threshold Voltage to enter Hiccup mode			2.85		v
T <sub>on_hi</sub> ccup	ON Time of Hiccup mode		70	130	190	ms
T <sub>off_hi</sub> ccup	OFF Time of Hiccup mode		0.7	1.3	1.9	s
		Thermal Shutdown				
	Temperature Rising Threshold			172		
	Hysteresis			20		°C



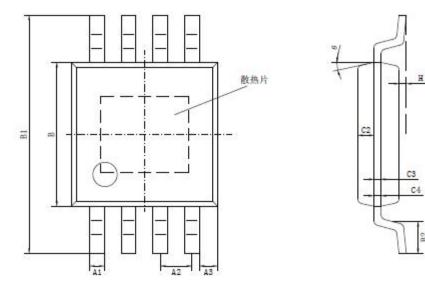
### **ELECTRICAL CHARACTERISTICS**

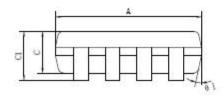
Conditions are:  $TA = 25^{\circ}C$ , VIN = SEL = 5.0 V, ENB = GND and  $RSET = 19.1 k\Omega$ . Positive current are into pins. All voltages are with respect to GND (unless otherwise noted).

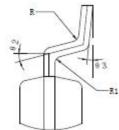
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
	UNDERVO	DLTAGE LOCKOUT		.1	<u>I</u>	
V <sub>UVLO</sub>	IN rising UVLO threshold voltage		3.75	3.95	4.15	V
	Hysteresis			100		mV
	SUPP	LY CURRENT				
I <sub>IN</sub>	IN supply current	VIN=5.0V, ENB=0V		160	280	
I <sub>DDL</sub>	IN Disable Supply Current	VIN=ENB=5.0V		0	2	μA
	BC 1.2 DC	CP MODE (SHORT)				
Rdpm_short	DP / DM shorting resistance			125	200	Ω
R <sub>DCHG_SHORT</sub>	Resistors connected DP /DM to GND after hand-shaking			200	400	kΩ
$V_{\text{DPL}_\text{TH}_\text{DETACH}}$	DP low threshold while detaching BC1.2 devices		310	330	350	mV
$V_{DPL_TH_DETACH_HYS}$	hysteresis			50		mV
	IPAD MODE 2.1A	A Mode (SEL=1 or Floati	ng)			
$V_{DP\_IPAD}$	DP output voltage		2.5	2.7	2.9	V
$V_{DM\_IPAD}$	DM output voltage		1.85	2.0	2.15	V
$R_{DP\_IPAD}$	DP output impedance	$I_{DP} = -5uA$	20	30	40	kΩ
R <sub>DM_IPAD</sub>	DM output impedance	$I_{DM} = -5uA$	20	30	40	kΩ
	IPAD MOD	E 2.4A Mode (SEL=0)		_		
$V_{DP\_IPAD}$	DP output voltage		2.5	2.7	2.9	V
$V_{DM\_IPAD}$	DM output voltage		2.5	2.7	2.9	V
R <sub>DP_IPAD</sub>	DP output impedance	$I_{DP} = -5uA$	20	30	40	kΩ
R <sub>DM_IPAD</sub>	DM output impedance	$I_{DM} = -5uA$	20	30	40	kΩ
	Gala	xy Tab MODE				
$V_{DP\_GAL}$	DP output voltage		1.1	1.2	1.3	v
$V_{DM\_GAL}$	DM output voltage		1.1	1.2	1.3	v
$R_{DP\_GAL}$	DP output impedance	$I_{DP} = -5uA$	70	105	140	kO
$R_{DM\_GAL}$	DM output impedance	$I_{DM} = -5uA$	70	105	140	kΩ



#### **PACKAGE INFORMATION** EMSOP8







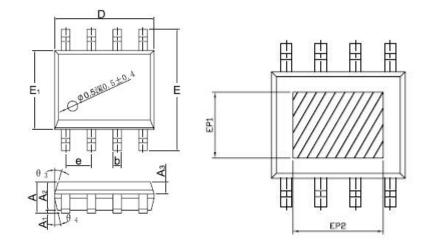
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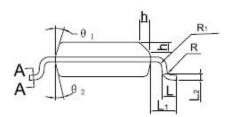
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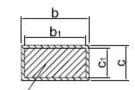
尺寸	最小(mm)	最大(mm)	标注	最小(mm)	最大(mm)	
A	2.90	3.20	CS	0.	152	
A1	0.28	0.35	C4	0.15	0.23	
A2	0.6	STYP	H	0.02	0.15	
A3	0.3	75TYP	θ	12	* TYP4	
В	2.90	3.20	01	12" IYP4		
B1	4.70	5.10	0 2	14° IYP		
B2	0.45	0.75	03	0° ~ 6°		
C	0.75	0.95	R	0.15TYP		
C1	( <u></u> )	1.10	R1	0.15TYP		
C2	0.3	28TYP		3045 mil		



### ESOP8







BASE METAL

SECTIONA-A 6:1 DIMENSIONS IN MUILLIMETERS

SYMBOL	MIN	NOM	MAX
A	1,35	1.55	1.75
A	0.00	I	0,10
Ax	1,25	1,40	1,65
A	0,50	0,60	0,70
р	0,39	l	0,49
P.	0,28	ļ	0,48
c	0,10	I	0,25
0	0,10	I	0,23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E.	3.80	3.90	4.00
6		1,278SC	
i.	0,45	1	1,00
Le		1,04REF	
L.		0.25BSC	
R	0,07	l	1
R	0,07	ļ	1
h	0,3	0,4	0,5
10.0	0*	I	8°
The second secon	110	17°	19°
0	11*	13*	15*
f .	15°	17*	19*
10.1	11*	13*	15*
EP1	2.40	<u> </u>	
EP2	3,30		